

1. Scope

The present specifications shall apply to an SJPX-F2.

2. Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	High Frequency Rectification

3. Flammability

UL94V-0(Equivalent)

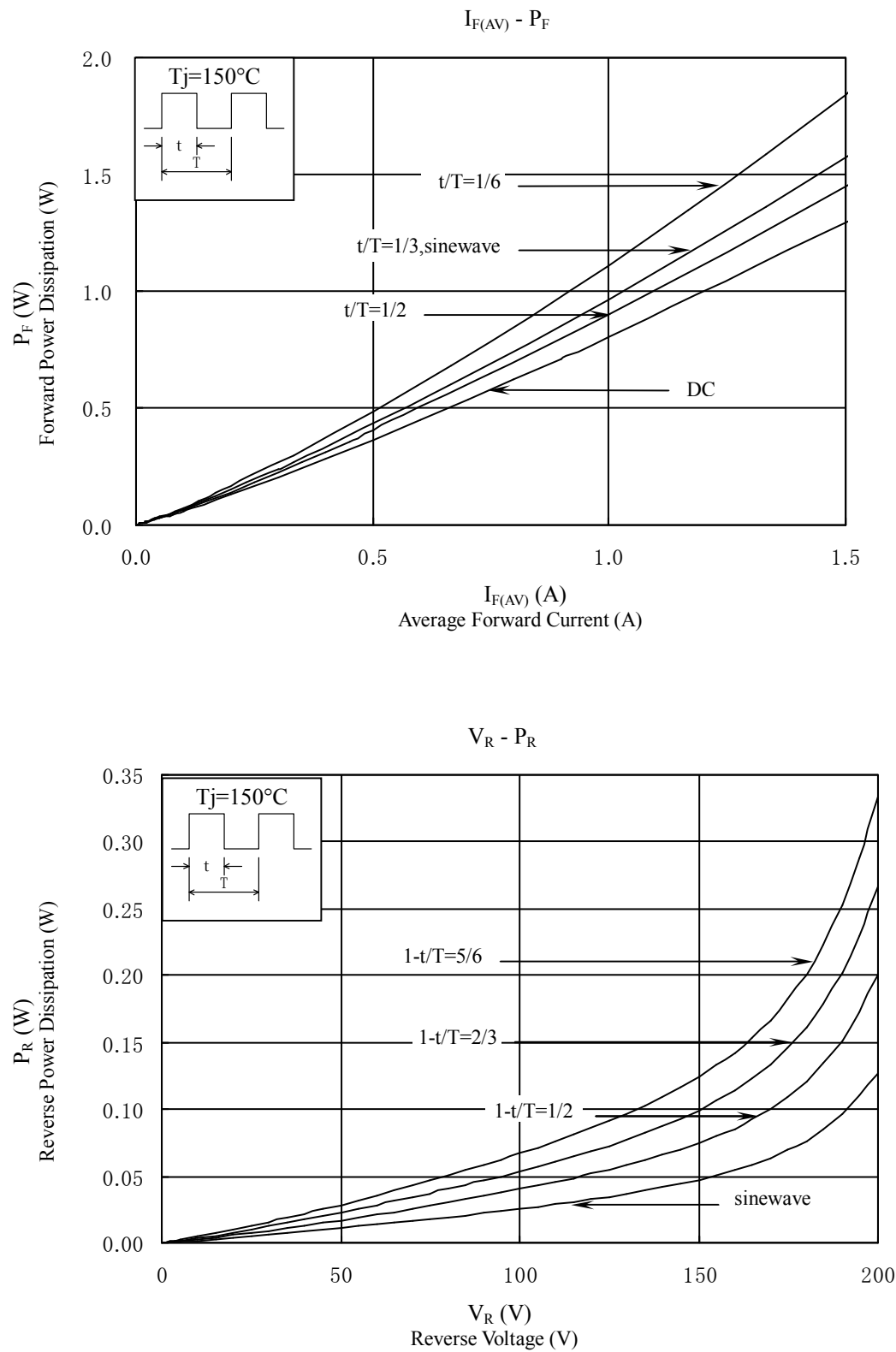
4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	200	
2	Peak Reverse Voltage	V_{RM}	V	200	
3	Average Forward Current	$I_{F(AV)}$	A	1.5	Refer to Derating of 7
4	Peak Surge Forward Current	I_{FSM}	A	30	10msec. Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A ² S	4.5	1msec $\leq t \leq$ 10msec
6	Junction Temperature	T_j	°C	-40~+150	
7	Storage Temperature	T_{stg}	°C	-40~+150	

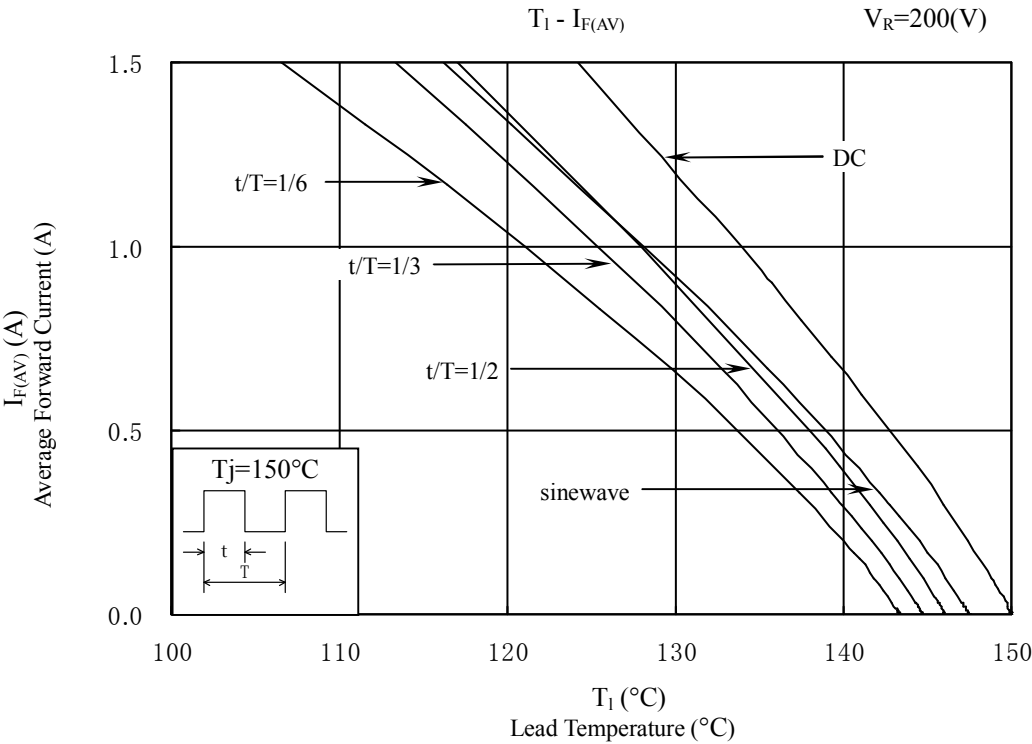
5. Electrical characteristics (Ta=25°C , unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	0.98 max.	$I_F=1.5A$
2	Reverse Leakage Current	I_R	uA	10 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	2 max.	$V_R=V_{RM}$, $T_j=150^\circ C$
4	Reverse Recovery Time	t_{rr1}	ns	30 max.	$I_F=I_{RP}=100mA$ 90% Recovery point, $T_j=25^\circ C$
		t_{rr2}	ns	25 max.	$I_F=100mA$, $I_{RP}=200mA$ 75% Recovery point, $T_j=25^\circ C$
5	Thermal Resistance	$R_{th(j-l)}$	°C/W	20 max.	Between Junction and Lead

6. Characteristics

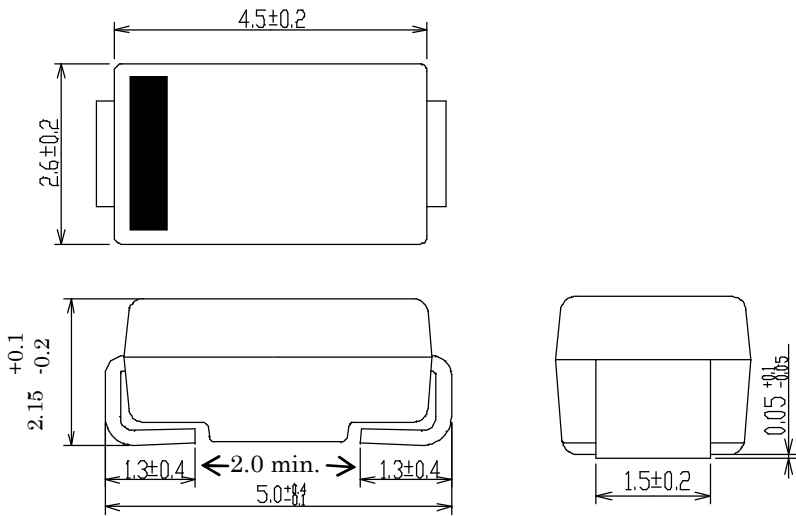


7. Derating



8. Package information

8-1Package type, physical dimensions and material

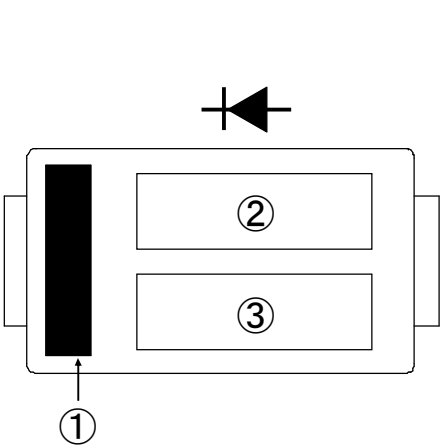


Dimensions in mm

8-2Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3Marking



① Polarity marking (Cathode band)

② Type number
SJPX-F2 as abbreviated of XF2

③ Lot number
Example) 6414
6: Last number of Year
4: Month from 1 to 9 for Jan. to Sep.
O for Oct., N for Nov., D for Dec.
14: Day